

FORM PTO 1449 (modified)

ATTY DOCKET NO.

03500.010530.4

APPLICATION NO.

09/161,774

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

APPLICANT

KIYOFUMI SAKAGUCHI, ET AL.

FILING DATE

September 29, 1998

GROUP

2823

LIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)

Submitted: November 25, 2003

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
G	4,116,751	09/26/78	Zaromb	156	600	
	4,727,047	02/23/88	Bozler, et al.	437	89	
	5,248,621	09/28/93	Sano	437	3	
	5,250,460	10/05/93	Yamagata, et al.	437	62	
	5,277,748	01/11/94	Sakaguchi, et al.	156	630	
	5,278,092	01/11/94	Sato	437	90	
	5,278,093	01/11/94	Yonehara	437	109	
	5,285,078	02/08/94	Mimura, et al.	257	3	
	5,290,712	03/01/94	Sato, et al.	437	24	
	5,320,907	06/14/94	Sato	428	446	
	5,331,180	07/19/94	Yamada, et al.	257	3	
	5,362,683	11/08/94	Takenaka, et al.	437	226	
	5,363,793	11/15/94	Sato	117	2	
	5,371,037	12/06/94	Yonehara	437	86	
	5,374,564	12/20/94	Bruel	437	24	
	5,403,771	04/04/95	Nishida, et al.	437	89	
	5,433,168	07/18/95	Yonehara	117	90	
	5,453,394	09/26/95	Yonehara, et al.	437	62	
	5,457,058	10/10/95	Yonehara	437	24	
	5,459,081	10/17/95	Kajita	437	3	
G	5,466,631	11/14/95	Ichikawa, et al.	437	62	
	5,536,361	07/16/96	Kondo, et al.	156	630.1	
EXAMINER	FOLKSON		DATE CONSIDERED	5/31/06		

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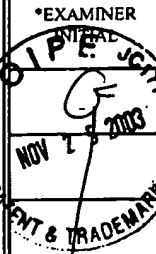
FORM PTO 1449 (modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary) Submitted: November 25, 2003				ATTY DOCKET NO. 03500.010530.4		APPLICATION NO. 09/161,774	
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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<div style="border: 1px solid black; border-radius: 50%; padding: 10px; display: inline-block; transform: rotate(-45deg);"> OIPE 38177 NOV 25 2003 PATENT & TRADEMARK OFFICE </div>		5,644,156	07/01/97	Suzuki, et al.	257	485	
		5,670,411	09/23/97	Yonehara, et al.	437	62	
		5,811,348	09/22/98	Matsushita, et al.	438	455	
		5,854,123	12/29/98	Sato, et al.	438	507	
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		6,103,598	08/15/00	Yamagata, et al.	438	459	
		6,107,213	08/22/00	Tayanaka	438	762	
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V		W.P. Maszara, "Silicon-On-Insulator by Wafer Bonding: A Review", J. Electrochem. Soc., vol. 138, No. 1, pp. 340-347 (1991)	
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Sheet 5 of 5

